

IN THE SPECIFICATION

Please amend the paragraph found on page 7, lines 19-26 of the specification (and on page 3, ¶[0034] of U.S. Application Publication No. 20040266179) as follows:

– With a positive resist, the exposed portions of photoresist **308** become soluble to a developer. As shown in FIGS. 3D 3C and 3E 3D, developing the wafer **302** provides templates for conductive rows. Generally, the wafer may be baked to harden the patterned photoresist **316**. The top surface of the wafer **302** is then etched such that the exposed portions of the conductive layer **304** are removed while the portions hidden beneath the patterned photoresist **316** remain. The wafer **302** may then be washed with a photoresist dissolving agent such that substantially all of the photoresist is removed and conductive rows **306** remain. –